FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office	Attorney Docket Number 5308-168	Serial No. 09/878,442
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)	Applicants: Das et al.	
	Filing Date: June 11, 2001	Group: 2815

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	1.	5,170,231	12/8/92	Fujii et al.	357	23.2	
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	3.	5,939,763	8/17/99	Hao et al.	257	411	
	4.	5,960,289	9/28/99	Tsui et al.	438	257	
	5.	5,972,801	10/26/99	Lipkin et al.	438	770	
	6.	6,028,012	2/22/00	Wang	438	779	
	7.	6,048,766	4/11/00	Gardner et al.	438	257	
	8.	6,054,352	4/25/00	Ueno	438	268	
	9.	6,063,698	5/16/00	Tseng et al.	438	585	
	10.	6,096,607	8/1/00	Ueno	438	522	
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	13.	6,165,822	12/26/00	Okuno et al.	438	142	
	14.	6,190,973 B1	2/20/01	Berg et al.	438	275	
	15.	6,204,203	3/01	Narwanker et al.	438	785	
	16.	6,211,035	4/01	Moise et al.	438	396	
	17.	6,221,700	4/24/01	Okuno et al.	438	151	
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	26	DE 198 09 554	9/10/98	Germany			Abstract
	27	DE 19900171	12/26/00	Germany			Abstract
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	29	JP 08264766	10/11/96	Japan			Abstract
	30	JP 09205202	8/5/97	Japan			Abstract
	31	JP 11191559	7/13/99	Japan			Abstract
	32	JP 11238742	8/31/99	Japan			Abstract
	33	JP 11261061	9/24/99	Japan			Abstract
	34	JP 11266017	9/28/99	Japan			Abstract
	35	JP 11274487	10/8/99	Japan			Abstract
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